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(54) **QUANTUM DOT LIGHT-EMITTING DIODE AND DISPLAY DEVICE**

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(57) **ABSTRACT**

This disclosure provides a quantum dot light-emitting diode comprising a first electron layer, an organic light-emitting layer, a first hole layer, a second electron layer, a quantum dot light-emitting layer, and a second hole layer. The first electron layer and the first hole layer are configured to transport first electrons and first holes to the organic light-emitting layer. The organic light-emitting layer is configured to emit a first light by recombining the first electrons and the first holes. The second electron layer and the second hole layer are configured to transport second electrons and second holes to the quantum dot light-emitting layer. The quantum dot light-emitting layer is configured to emit a second light by recombining the second electrons and the second holes.

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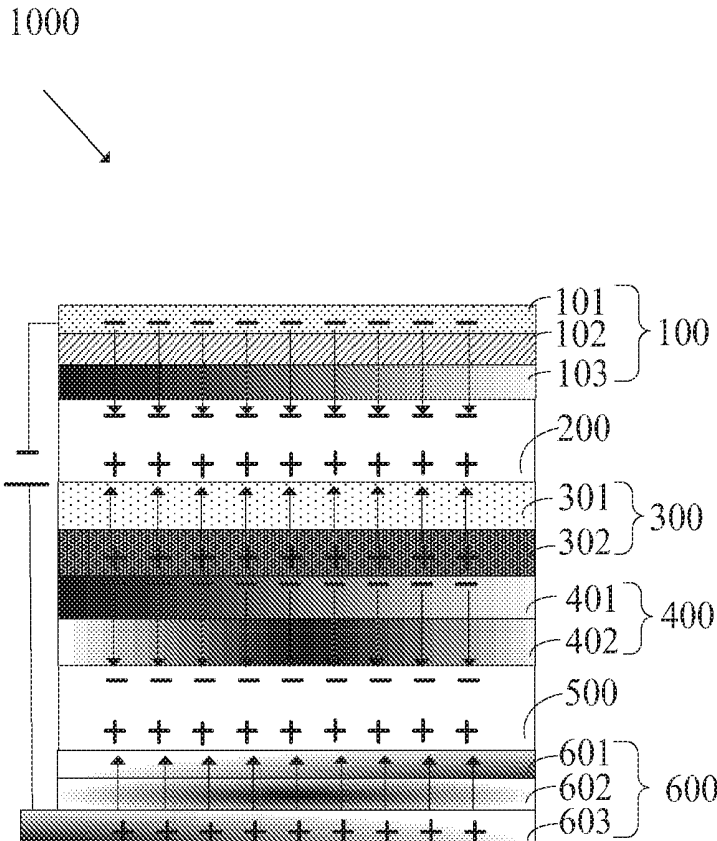
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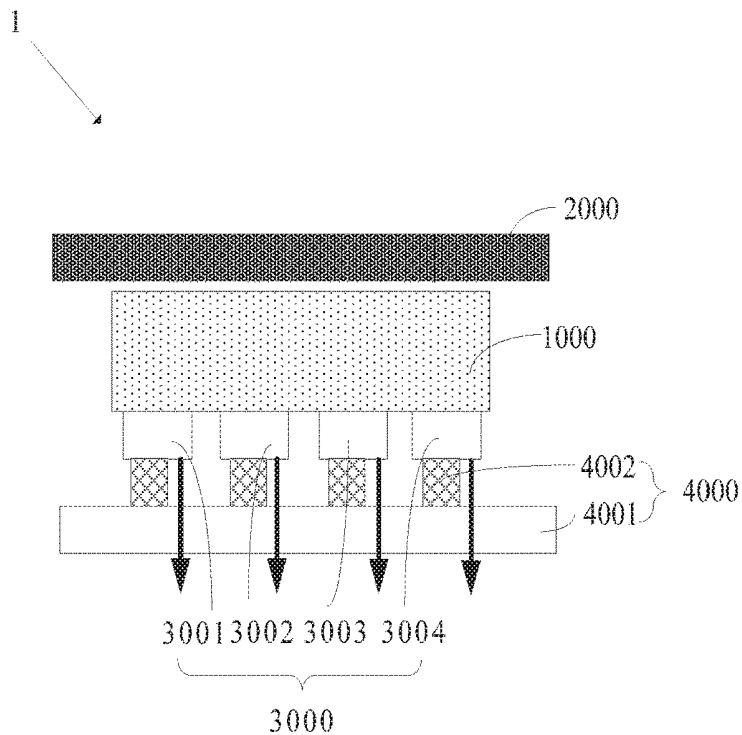


FIG. 1

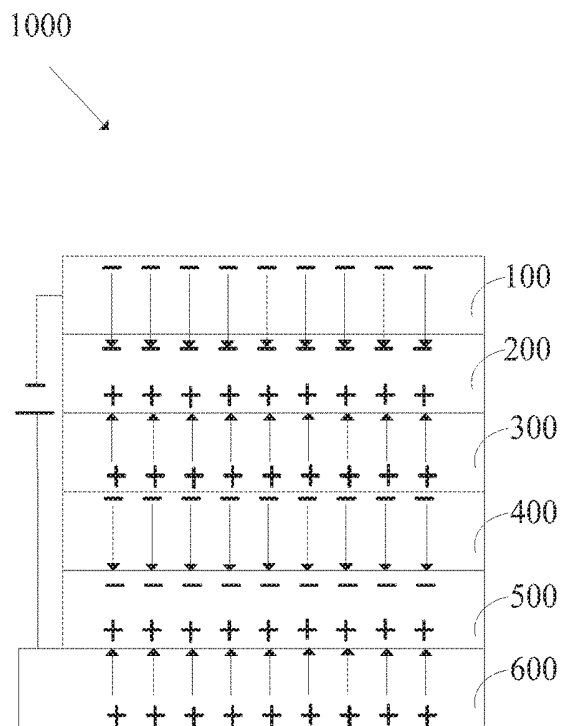


FIG. 2

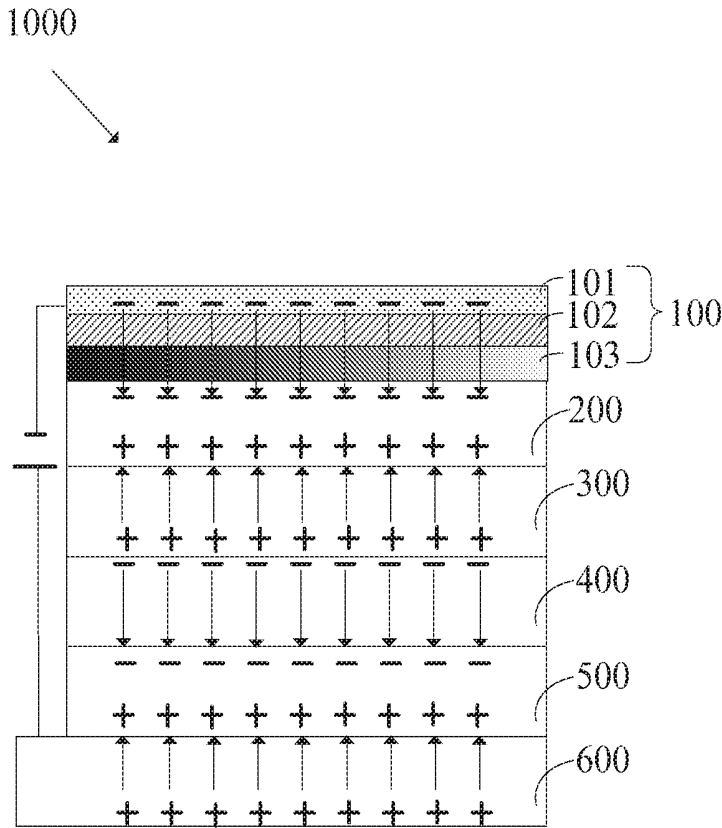


FIG. 3

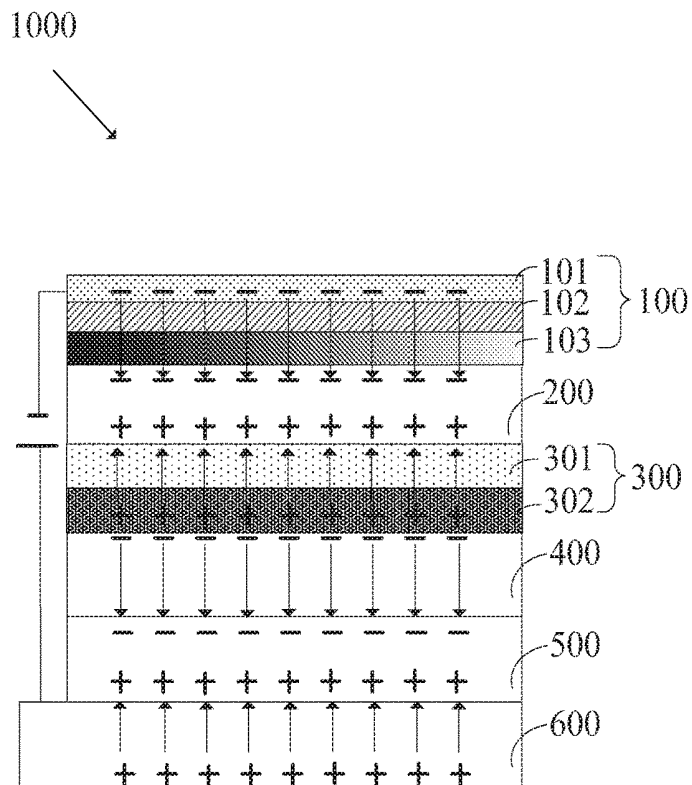


FIG. 4

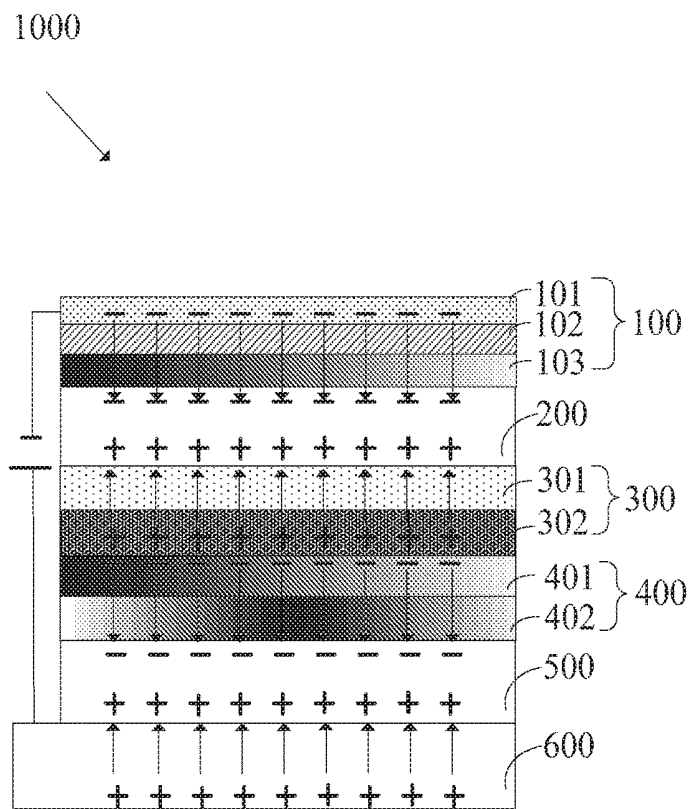


FIG. 5

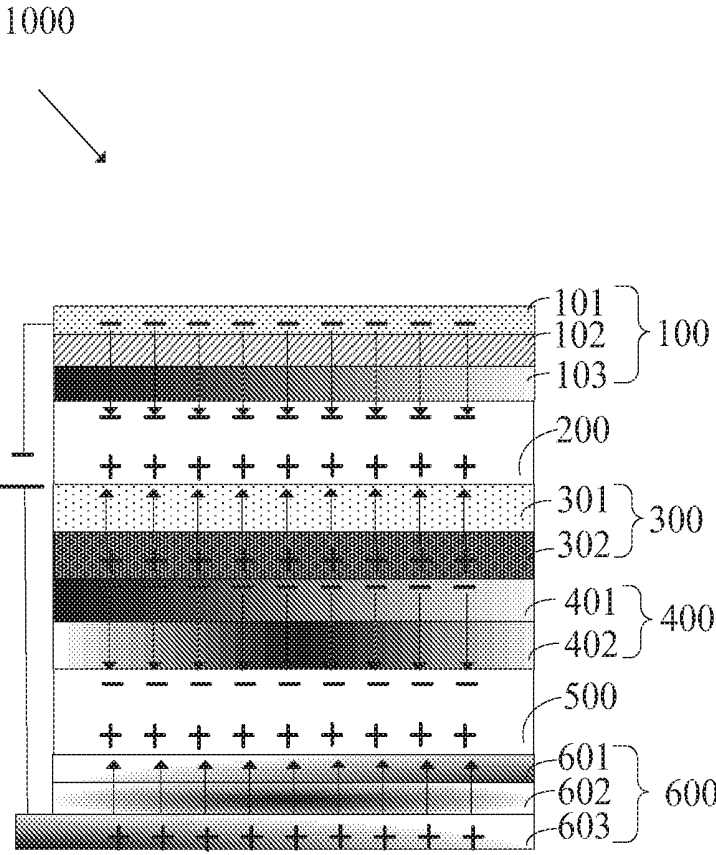


FIG. 6

QUANTUM DOT LIGHT-EMITTING DIODE AND DISPLAY DEVICE

BACKGROUND

1. Field of the Invention

[0001] The present disclosure relates to the field of display technology, and more particularly to a quantum dot light-emitting diode and a display device.

2. Description of the Prior Art

[0002] Wavelength of quantum dot material, having advantages of a broad excitation spectrum, a high electron mobility, and a high light purity, may be varied with size of the quantum dot materials. Thus, the quantum dot materials are widely used in display devices.

[0003] In quantum dot liquid crystal display technology, quantum dot materials are used in backlights of liquid crystal displays. Luminescence properties of quantum dots emit a red light and a green light under a light irradiation of a blue light-emitting diode. The red light, the green light and a blue light pass through a thin film and are recombined to form a white light and make the backlight of the liquid crystal displays have a remarkable luminous effect.

[0004] Quantum dot light-emitting diode technology is a real self-luminous display technology compared to the quantum dot liquid crystal technology which only has a remarkable luminous effect. A quantum dot layer is disposed between an electron transmission layer and a hole transmission layer in the quantum dot light-emitting diode technology. Electrons and holes are transported to the quantum dot layer in response to an applied electric. Carriers are recombined to form excitons seized by the quantum dot light-emitting materials to emit a light. The quantum dot light-emitting diodes of the present disclosure can realize self-luminosity, but also the quantum dot light-emitting has a short lifespan.

SUMMARY

[0005] The present disclosure provides a quantum dot light-emitting diode and a display device to make a longer lifespan of the quantum dot light-emitting diode.

[0006] The present disclosure provides a quantum dot light-emitting diode, comprising a first electron layer, an organic light-emitting layer, a first hole layer, a second electron layer, a quantum dot light-emitting layer, and a second hole layer that are sequentially stacked;

[0007] wherein the first electron layer is configured to transport first electrons to the organic light-emitting layer;

[0008] wherein the first hole layer is configured to transport first holes to the organic light-emitting layer;

[0009] wherein the organic light-emitting layer is configured to emit a first light by recombining the first electrons and the first holes;

[0010] wherein the second electron layer is configured to transport second electrons to the quantum dot light-emitting layer;

[0011] wherein the second hole layer is configured to transport second holes to the quantum dot light-emitting layer;

[0012] wherein the quantum dot light-emitting layer is configured to emit a second light by recombining the second electrons and the second holes.

[0013] According to some disclosures, doped dyes of the organic light-emitting layer comprise one or more selected from a group consisting of ASP-f, Blvd, and TPATAZ, host materials of the organic light-emitting layer comprise one or more selected from a group consisting of CBP, Taco, and TMPyPb, a thickness of the organic light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the first light emitted from the organic light-emitting layer ranges from 450 nm to 480 nm.

[0014] According to some disclosures, component materials of the quantum dot light-emitting layer comprise one or more selected from a group consisting of CdSe/ZnS, CdS/ZnS, CdSe/ZnSe, and CdS/ZnSe, a particle size of the component materials ranges from 2 nm to 5 nm, a thickness of the quantum dot light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the second light emitted from the quantum dot light-emitting layer ranges from 540 nm to 570 nm.

[0015] According to some disclosures, the first electron layer comprises a cathode, an electron injection layer and a first electron transmission layer that are sequentially stacked, and the first electron transmission layer is disposed on the organic light-emitting layer;

[0016] wherein the cathode is configured to provide the first electrons;

[0017] wherein the electron injection layer is configured to transport the first electrons to the first electron transmission layer;

[0018] wherein the first electron transmission layer is configured to transport the first electrons to the organic light-emitting layer.

[0019] According to some disclosures, component materials of the cathode comprise one or more selected from a group consisting of Li, Mg, Ca, Sr, La, Ce, Eu, Yb, Al, Cs, Rb, and Ag, and a thickness of the cathode ranges from 50 nm to 200 nm;

[0020] wherein component materials of the electron injection layer comprise one or more selected from a group consisting of LiF, NaF, and Liq, and a thickness of the electron injection layer ranges from 0.5 nm to 3 nm;

[0021] wherein component materials of the first electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPB1, and TPyPhB, and a thickness of the first electron transmission layer ranges from 20 nm to 60 nm.

[0022] According to some disclosures, the first hole layer comprises a first hole transmission layer and an hole generating layer disposed on the second electron layer;

[0023] wherein the hole generating layer is configured to provide the first holes;

[0024] wherein the first hole transmission layer is configured to transport the first holes to the organic light-emitting layer.

[0025] According to some disclosures, component materials of the first hole transmission layer comprise one or more selected from a group consisting of NPB, TDAPB, PIDATA, TDAB, BFA-1T, and TPTE, and a thickness of the first hole transmission layer ranges from 10 nm to 60 nm;

- [0026] wherein component materials of the hole generating layer comprise one or more selected from a group consisting of HATCN, CuPc, and 2-TNATA, and a thickness of the hole generating layer ranges from 5 nm to 50 nm.
- [0027] According to some disclosures, the second electron layer comprises an electron generating layer and a second electron transmission layer disposed on the quantum dot light-emitting layer;
- [0028] wherein the electron generating layer is configured to provide the second electrons;
- [0029] wherein the second electron transmission layer is configured to transport the second electrons to the quantum dot light-emitting layer.
- [0030] According to some disclosures, component materials of the electron generating layer comprise organic materials and metal materials, and a thickness of the electron generating layer ranges from 5 nm to 50 nm;
- [0031] wherein component materials of the second electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPBI, and TPyPhB, and a thickness of the second electron transmission layer ranges from 20 nm to 60 nm.
- [0032] According to some disclosures, the second hole layer comprises an anode, a hole injection layer and a second hole transmission layer that are sequentially stacked, and the quantum dot light-emitting layer is disposed on the second hole transmission layer;
- [0033] wherein the anode is configured to provide the second holes;
- [0034] wherein the hole injection layer is configured to transport the second holes to the second hole transmission layer;
- [0035] wherein the second hole transmission layer is configured to transport the second holes to the quantum dot light-emitting layer.
- [0036] According to some disclosures, component materials of the hole injection layer comprise PEDOT:PSS, and a thickness of the hole injection ranges from 5 nm to 60 nm;
- [0037] wherein component materials of the second hole transmission layer comprise one or more selected from a group consisting of PVK, TFB, and Poly-TPD, and a thickness of the second hole transmission layer ranges from 10 nm to 60 nm.
- [0038] The present disclosure provides a display device, comprising a cover plate, a quantum dot light-emitting diode, a color filter unit and a substrate that are sequentially stacked, and the quantum dot light-emitting diode comprises a first electron layer, an organic light-emitting layer, a first hole layer, a second electron layer, a quantum dot light-emitting layer, and a second hole layer that are sequentially stacked;
- [0039] wherein the first electron layer is configured to transport first electrons to the organic light-emitting layer;
- [0040] wherein the first hole layer is configured to transport first holes to the organic light-emitting layer;
- [0041] wherein the organic light-emitting layer is configured to emit a first light by recombining the first electrons and the first holes;
- [0042] wherein the second electron layer is configured to transport second electrons to the quantum dot light-emitting layer;
- [0043] wherein the second hole layer is configured to transport second holes to the quantum dot light-emitting layer;
- [0044] wherein the quantum dot light-emitting layer is configured to emit a second light by recombining the second electrons and the second holes.
- [0045] According to some disclosures, doped dyes of the organic light-emitting layer comprise one or more selected from a group consisting of DSP-ph, DPVB1, and TPATAZ, host materials of the organic light-emitting layer comprise one or more selected from a group consisting of CBP, TcTa, and TMPyPb, a thickness of the organic light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the first light emitted from the organic light-emitting layer ranges from 450 nm to 480 nm.
- [0046] According to some disclosures, component materials of the quantum dot light-emitting layer comprise one or more selected from a group consisting of CdSe/ZnS, CdS/ZnS, CdSe/ZnSe, and CdS/ZnSe, a particle size of the component materials ranges from 2 nm to 5 nm, a thickness of the quantum dot light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the second light emitted from the quantum dot light-emitting layer ranges from 540 nm to 570 nm.
- [0047] According to some disclosures, the first electron layer comprises a cathode, an electron injection layer and a first electron transmission layer that are sequentially stacked, and the first electron transmission layer is disposed on the organic light-emitting layer;
- [0048] wherein the cathode is configured to provide the first electrons;
- [0049] wherein the electron injection layer is configured to transport the first electrons to the first electron transmission layer;
- [0050] wherein the first electron transmission layer is configured to transport the first electrons to the organic light-emitting layer.
- [0051] According to some disclosures, component materials of the cathode comprise one or more selected from a group consisting of Li, Mg, Ca, Sr, La, Ce, Eu, Yb, Al, Cs, Rb, and Ag, and a thickness of the cathode ranges from 50 nm to 200 nm;
- [0052] wherein component materials of the electron injection layer comprise one or more selected from a group consisting of LiF, NaF, and Liq, and a thickness of the electron injection layer ranges from 0.5 nm to 3 nm;
- [0053] wherein component materials of the first electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPBI, and TPyPhB, and a thickness of the first electron transmission layer ranges from 20 nm to 60 nm.
- [0054] According to some disclosures, the first hole layer comprises a first hole transmission layer and an hole generating layer disposed on the second electron layer;
- [0055] wherein the hole generating layer is configured to provide the first holes;
- [0056] wherein the first hole transmission layer is configured to transport the first holes to the organic light-emitting layer.
- [0057] According to some disclosures, component materials of the first hole transmission layer comprise one or more selected from a group consisting of NPB, TDAPB,

PIDATA, TDAB, BFA-1T, and TPTE, and a thickness of the first hole transmission layer ranges from 10 nm to 60 nm;

[0058] wherein component materials of the hole generating layer comprise one or more selected from a group consisting of HATCN, CuPc, and 2-TNATA, and a thickness of the hole generating layer ranges from 5 nm to 50 nm.

[0059] According to some disclosures, the second electron layer comprises an electron generating layer and a second electron transmission layer disposed on the quantum dot light-emitting layer;

[0060] wherein the electron generating layer is configured to provide the second electrons;

[0061] wherein the second electron transmission layer is configured to transport the second electrons to the quantum dot light-emitting layer.

[0062] According to some disclosures, component materials of the electron generating layer comprise organic materials and metal materials, and a thickness of the electron generating layer ranges from 5 nm to 50 nm;

[0063] wherein component materials of the second electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPBI, and TPyPhB, and a thickness of the second electron transmission layer ranges from 20 nm to 60 nm.

[0064] Compared to the existing quantum dot light-emitting diode and the existing display device, the present disclosure set up the organic light-emitting layer, the quantum dot light-emitting layer, two electron layers, and two hole layers to make the quantum dot light-emitting diode a longer lifespan, wherein the two electron layers emits electrons to the organic light-emitting layer and the quantum dot light-emitting layer, respectively, and the two hole layers emits holes to the organic light-emitting layer and the quantum dot light-emitting layer, respectively.

[0065] Aforementioned contents of the present disclosure will be a better understood with reference to the following description, appended claims and accompanying figures.

BRIEF DESCRIPTION OF THE DRAWINGS

[0066] FIG. 1 is a structural schematic diagram of a display device according to the present disclosure.

[0067] FIG. 2 is a first structural schematic diagram of a quantum dot light-emitting diode according to the present disclosure.

[0068] FIG. 3 is a second structural schematic diagram of a quantum dot light-emitting diode according to the present disclosure.

[0069] FIG. 4 is a third structural schematic diagram of a quantum dot light-emitting diode according to the present disclosure.

[0070] FIG. 5 is a fourth structural schematic diagram of a quantum dot light-emitting diode according to the present disclosure.

[0071] FIG. 6 is a fifth structural schematic diagram of a quantum dot light-emitting diode according to the present disclosure.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0072] The following description of every embodiment with reference to the accompanying drawings is used to

exemplify a specific embodiment which may be carried out in the present disclosure. Directional terms mentioned in the present disclosure, such as “top”, “bottom”, “front”, “back”, “left”, “right”, “inside”, “outside”, “side” etc., are only used with reference to the orientation of the accompanying drawings. Therefore, the used directional terms are intended to illustrate, but not to limit, the present disclosure. In the accompanying drawings, units with similar structures are indicated by the same sign.

[0073] Reference throughout the specification to “embodiment” means that a particular feature, structure, or characteristic described in connection with the embodiment is included in at least one embodiment. Thus, appearances of the phrases “embodiment” in places throughout the specification are may be combined in any suitable manner in one or more embodiments. Thus, the particular features, structures, or characteristics illustrated or described in connection with one embodiment may be combined, in whole or in part, with the features structures, or characteristics of one or more other embodiments without limitation. Such modifications and variations are intended to be included within the scope of the present invention.

[0074] As shown in FIG. 1, FIG. 1 is a structural schematic diagram of a display device according to the present disclosure. The display device 1 comprises a cover plate 2000, a quantum dot light-emitting diode 1000, a color filter unit 3000 and a substrate 4000 that are sequentially stacked.

[0075] The color filter unit 3000 comprises a plurality of red sub-pixels 3001 filtering a red light out, a plurality of green sub-pixels 3002 filtering a green light out, a plurality of blue sub-pixels 3003 filtering a blue light out, and a plurality of white sub-pixels 3004 filtering a white light out, wherein the plurality of white sub-pixels 3004 have no filter layer. The substrate 400 comprises a base substrate 4001 and a plurality of field effect transistors 4001 disposed on the base substrate 4001. Each field effect transistor 4001 comprises a semiconductor layer, an insulating layer, a source electrode, a drain electrode and a gate electrode. It should be noted that packaging adhesives disposed between the cover plate 2000 and the substrate 4000 are used to protect the quantum dot light-emitting diode from water and oxygen.

[0076] As shown in FIG. 2, FIG. 2 is a structural schematic diagram of a quantum dot light-emitting diode according to the present disclosure. The quantum dot light-emitting diode 1000 comprise a first electron layer 100, an organic light-emitting layer 200, a first hole layer 300, a second electron layer 400, a quantum dot light-emitting layer 500, and a second hole layer 600 that are sequentially stacked.

[0077] The first electron layer 100 is configured to transport first electrons to the organic light-emitting layer 200, the first hole layer 300 is configured to transport first holes to the organic light-emitting layer 200, and the organic light-emitting layer 200 is configured to emit a first light by recombining the first electrons and the first holes. The second electron layer 400 is configured to transport second electrons to the quantum dot light-emitting layer 500, the second hole layer 600 is configured to transport second holes to the quantum dot light-emitting layer, and the quantum dot light-emitting layer 500 is configured to emit a second light by recombining the second electrons and the second holes.

[0078] As shown in FIG. 3, the first electron layer 100 comprises a cathode 100, an electron injection layer 102 and a first electron transmission layer 103 that are sequentially

stacked, wherein the first electron transmission layer **103** is disposed on the organic light-emitting layer **200**.

[0079] The cathode **101** is configured to provide the first electrons. The cathode **101** is made of low work function metals, and component materials of the cathode **101** comprise one or more selected from a group consisting of Li, Mg, Ca, Sr, La, Ce, Eu, Yb, Al, Cs, Rb and Ag. The cathode **101** is formed by a process of vacuum evaporation, and a thickness of the cathode **101** ranges from 50 nm to 200 nm.

[0080] The electron injection layer **102** is configured to transport the first electrons to the first electron transmission layer **103**. Component materials of the electron injection layer **102** comprise one or more selected from a group consisting of LiF, NaF, and Liq. The electron injection layer **102** is formed by a process of evaporation, and a thickness of the electron injection layer **102** ranges from 0.5 nm to 3 nm.

[0081] The first electron transmission layer **103** is configured to transport the first electrons to the organic light-emitting layer **200**. Component materials of the first electron transmission layer **103** comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPBI, and TPyPhB. The first electron transmission layer **103** is formed by a process of evaporation, and a thickness of the first electron transmission layer **103** ranges from 20 nm to 60 nm.

[0082] The organic light-emitting layer **200** comprises a blue organic light-emitting layer. And the first light emitted from the organic light-emitting layer **200** by recombining the first electrons and the first holes is a blue light. Doped dyes of the organic light-emitting layer **200** comprise one or more selected from a group consisting of DSP-ph, DPVB1, and TPATAZ, and host materials of the organic light-emitting layer **200** comprise one or more selected from a group consisting of CBP, TcTa, and TmPyPb. The organic light-emitting layer **200** is formed by a process of evaporation, and a thickness of the organic light-emitting layer **200** ranges from 20 nm to 40 nm, and a wavelength of the first light emitted from the organic light-emitting layer **200** ranges from 450 nm to 480 nm. The organic light-emitting layer **200** is disposed to make the quantum dot light-emitting diode a long lifespan according to the present disclosure.

[0083] As shown in FIG. 4, the first hole layer **300** comprises a first hole transmission layer **301** and an hole generating layer **302** disposed on the second electron layer **400**.

[0084] The hole generating layer **302** is configured to provide the first holes. Component materials of the hole generating layer **302** comprise one or more selected from a group consisting of HATCN, CuPc, and 2-TNATA. The hole generating layer is formed by a process of evaporation, and a thickness of the hole generating layer ranges from 5 nm to 50 nm.

[0085] The first hole transmission layer **301** is configured to transport the first holes to the organic light-emitting layer **200**. Component materials of the first hole transmission layer **301** comprise one or more selected from a group consisting of NPB, TDAPB, PIDATA, TDAB, BFA-1T, and TPTE. The first hole transmission layer **301** is formed by a process of evaporation, and a thickness of the first hole transmission layer **301** ranges from 10 nm to 60 nm.

[0086] As shown in FIG. 5, the second electron layer **400** comprises an electron generating layer **401** and a second electron transmission layer **402** disposed on the quantum dot light-emitting layer **500**.

[0087] The electron generating layer **401** is configured to provide the second electrons. Component materials of the electron generating layer **401** comprise metal materials and organic materials comprising one or more selected from a group consisting of Bphen:Li and Bphen:Yb. The electron generating layer is formed by a process of evaporation and a thickness of the electron generating layer ranges from 5 nm to 50 nm.

[0088] The second electron transmission layer **402** is configured to transport the second electrons to the quantum dot light-emitting layer **500**. Component materials of the second electron transmission layer **402** comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPBI, and TPyPhB. The second electron transmission layer **402** is formed by a process of evaporation, and a thickness of the second electron transmission layer **402** ranges from 20 nm to 60 nm.

[0089] The quantum dot light-emitting layer **500** comprises a yellow quantum dot light-emitting layer. And the second light emitted from the quantum dot light-emitting layer **500** by recombining the second electrons and the second holes is a yellow light. Component materials of the quantum dot light-emitting layer **500** comprise one or more selected from a group yellow quantum dot light-emitting materials with core shell structure consisting of CdSe/ZnS, CdS/ZnS, CdSe/ZnSe, and CdS/ZnSe, and a particle size of the component materials ranges from 2 nm to 5 nm. The quantum dot light-emitting layer **500** is formed by a process of spin coating or nozzle printing, and a thickness of the quantum dot light-emitting layer **500** ranges from 20 nm to 40 nm. A wavelength of the second light emitted from the quantum dot light-emitting layer **500** ranges from 540 nm to 570 nm.

[0090] As shown in FIG. 6, the second hole layer **600** comprises an anode **603**, an hole injection layer **602** and a second hole transmission layer **601** that are sequentially stacked, and the quantum dot light-emitting layer **500** is disposed on the second hole transmission layer **601**. The anode **603** is made by ITO and configured to provide the second holes.

[0091] The hole injection layer **602** is configured to transport the second holes to the second hole transmission layer **601**. Component materials of the hole injection layer comprise PEDOT:PSS. The hole injection layer **602** is formed by a process of spin coating or nozzle printing, and a thickness of the hole injection **602** ranges from 5 nm to 60 nm.

[0092] The second hole transmission layer **601** is configured to transport the second holes to the quantum dot light-emitting layer **500**. Component materials of the second hole transmission layer **601** comprise one or more selected from a group consisting of PVK, TFB, and Poly-TPD. The second hole transmission layer **602** is formed by a process of spin coating or nozzle printing, and a thickness of the second hole transmission layer **602** ranges from 10 nm to 60 nm.

[0093] The present disclosure set up the organic light-emitting layer, the quantum dot light-emitting layer, two electron layers, and two hole layers to make the quantum dot light-emitting diode a longer lifespan, wherein the two electron layers emits electrons to the organic light-emitting

layer and the quantum dot light-emitting layer, respectively, and the two hole layers emits holes to the organic light-emitting layer and the quantum dot light-emitting layer, respectively.

[0094] The present disclosure is described in detail in accordance with the above contents with the specific preferred examples. However, this present disclosure is not limited to the specific examples. For a person of ordinary skill in the art, on the premise of keeping the conception of the present disclosure, the technical personnel can also make simple deductions or replacements, all of which should be considered to belong to the protection scope of the present disclosure.

1. A quantum dot light-emitting diode, comprising: a first electron layer, an organic light-emitting layer, a first hole layer, a second electron layer, a quantum dot light-emitting layer, and a second hole layer that are sequentially stacked;

wherein the first electron layer is configured to transport first electrons to the organic light-emitting layer;

wherein the first hole layer is configured to transport first holes to the organic light-emitting layer;

wherein the first electrons and the first holes are recombined in the organic light-emitting layer to form excitons, and the organic light-emitting layer is configured to emit a first light using energy generated by the excitons;

wherein the second electron layer is configured to transport second electrons to the quantum dot light-emitting layer;

wherein the second hole layer is configured to transport second holes to the quantum dot light-emitting layer;

wherein the second electrons and the second holes are recombined in the quantum dot light-emitting layer to form excitons, and the quantum dot light-emitting layer is configured to emit a second light using energy generated by the excitons.

2. The quantum dot light-emitting diode as claimed in claim 1, wherein doped dyes of the organic light-emitting layer comprise one or more selected from a group consisting of ASP-f, Blvd, and TPATAZ, host materials of the organic light-emitting layer comprise one or more selected from a group consisting of CBP, Taco, and TMPyPb, a thickness of the organic light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the first light emitted from the organic light-emitting layer ranges from 450 nm to 480 nm.

3. The quantum dot light-emitting diode as claimed in claim 1, wherein component materials of the quantum dot light-emitting layer comprise one or more selected from a group consisting of CdSe/ZnS, CdS/ZnS, CdSe/ZnSe, and CdS/ZnSe, a particle size of the component materials ranges from 2 nm to 5 nm, a thickness of the quantum dot light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the second light emitted from the quantum dot light-emitting layer ranges from 540 nm to 570 nm.

4. The quantum dot light-emitting diode as claimed in claim 1, wherein the first electron layer comprises a cathode, an electron injection layer and a first electron transmission layer that are sequentially stacked, and the first electron transmission layer is disposed on the organic light-emitting layer;

wherein the cathode is configured to provide the first electrons;

wherein the electron injection layer is configured to transport the first electrons to the first electron transmission layer;

wherein the first electron transmission layer is configured to transport the first electrons to the organic light-emitting layer.

5. The quantum dot light-emitting diode as claimed in claim 4, wherein component materials of the cathode comprise one or more selected from a group consisting of Li, Mg, Ca, Sr, La, Ce, Eu, Yb, Al, Cs, Rb, and Ag, and a thickness of the cathode ranges from 50 nm to 200 nm;

wherein component materials of the electron injection layer comprise one or more selected from a group consisting of LiF, NaF, and Liq, and a thickness of the electron injection layer ranges from 0.5 nm to 3 nm;

wherein component materials of the first electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPBI, and TPyPhB, and a thickness of the first electron transmission layer ranges from 20 nm to 60 nm.

6. The quantum dot light-emitting diode as claimed in claim 1, wherein the first hole layer comprises a first hole transmission layer and an hole generating layer disposed on the second electron layer;

wherein the hole generating layer is configured to provide the first holes;

wherein the first hole transmission layer is configured to transport the first holes to the organic light-emitting layer.

7. The quantum dot light-emitting diode as claimed in claim 6, wherein component materials of the first hole transmission layer comprise one or more selected from a group consisting of NPB, TDAPB, PIDATA, TDAB, BFA-IT, and TPTE, and a thickness of the first hole transmission layer ranges from 10 nm to 60 nm;

wherein component materials of the hole generating layer comprise one or more selected from a group consisting of HATCN, CuPc, and 2-TNATA, and a thickness of the hole generating layer ranges from 5 nm to 50 nm.

8. The quantum dot light-emitting diode as claimed in claim 1, wherein the second electron layer comprises an electron generating layer and a second electron transmission layer disposed on the quantum dot light-emitting layer;

wherein the electron generating layer is configured to provide the second electrons;

wherein the second electron transmission layer is configured to transport the second electrons to the quantum dot light-emitting layer.

9. The quantum dot light-emitting diode as claimed in claim 8, wherein component materials of the electron generating layer comprise organic materials and metal materials, and a thickness of the electron generating layer ranges from 5 nm to 50 nm;

wherein component materials of the second electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPBI, and TPyPhB, and a thickness of the second electron transmission layer ranges from 20 nm to 60 nm.

10. The quantum dot light-emitting diode as claimed in claim 1, wherein the second hole layer comprises an anode, an hole injection layer and a second hole transmission layer

that are sequentially stacked, and the quantum dot light-emitting layer is disposed on the second hole transmission layer;

wherein the anode is configured to provide the second holes;

wherein the hole injection layer is configured to transport the second holes to the second hole transmission layer;

wherein the second hole transmission layer is configured to transport the second holes to the quantum dot light-emitting layer.

11. The quantum dot light-emitting diode as claimed in claim **10**, wherein component materials of the hole injection layer comprise PEDOT:PSS, and a thickness of the hole injection ranges from 5 nm to 60 nm;

wherein component materials of the second hole transmission layer comprise one or more selected from a group consisting of PVK, TFB, and Poly-TPD, and a thickness of the second hole transmission layer ranges from 10 nm to 60 nm.

12. A display device, comprising a cover plate, a quantum dot light-emitting diode, a color filter unit and a substrate that are sequentially stacked, and the quantum dot light-emitting diode comprises a first electron layer, an organic light-emitting layer, a first hole layer, a second electron layer, a quantum dot light-emitting layer, and a second hole layer that are sequentially stacked;

wherein the first electron layer is configured to transport first electrons to the organic light-emitting layer;

wherein the first hole layer is configured to transport first holes to the organic light-emitting layer;

wherein the first electrons and the first holes are compounded in the organic light-emitting layer to form excitons, and the organic light-emitting layer is configured to emit a first light using energy generated by the excitons;

wherein the second electron layer is configured to transport second electrons to the quantum dot light-emitting layer;

wherein the second hole layer is configured to transport second holes to the quantum dot light-emitting layer;

wherein the second electrons and the second holes are compounded in the quantum dot light-emitting layer to form excitons, and the quantum dot light-emitting layer is configured to emit a second light using energy generated by the excitons.

13. The display device as claimed in claim **12**, wherein doped dyes of the organic light-emitting layer comprise one or more selected from a group consisting of DSP-ph, DPVB1, and TPATAZ, host materials of the organic light-emitting layer comprise one or more selected from a group consisting of CBP, TcTa, and TmPyPb, a thickness of the organic light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the first light emitted from the organic light-emitting layer ranges from 450 nm to 480 nm.

14. The quantum dot light-emitting diode as claimed in claim **1**, wherein component materials of the quantum dot light-emitting layer comprise one or more selected from a group consisting of CdSe/ZnS, CdS/ZnS, CdSe/ZnSe, and CdS/ZnSe, a particle size of the component materials ranges from 2 nm to 5 nm, a thickness of the quantum dot light-emitting layer ranges from 20 nm to 40 nm, and a wavelength of the second light emitted from the quantum dot light-emitting layer ranges from 540 nm to 570 nm.

15. The display device as claimed in claim **12**, wherein the first electron layer comprises a cathode, an electron injection layer and a first electron transmission layer that are sequentially stacked, and the first electron transmission layer is disposed on the organic light-emitting layer;

wherein the cathode is configured to provide the first electrons;

wherein the electron injection layer is configured to transport the first electrons to the first electron transmission layer;

wherein the first electron transmission layer is configured to transport the first electrons to the organic light-emitting layer.

16. The display device as claimed in claim **15**, wherein component materials of the cathode comprise one or more selected from a group consisting of Li, Mg, Ca, Sr, La, Ce, Eu, Yb, Al, Cs, Rb, and Ag, and a thickness of the cathode ranges from 50 nm to 200 nm;

wherein component materials of the electron injection layer comprise one or more selected from a group consisting of LiF, NaF, and Liq, and a thickness of the electron injection layer ranges from 0.5 nm to 3 nm;

wherein component materials of the first electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ, OXD-7, TAZ, TPB1, and TPyPhB, and a thickness of the first electron transmission layer ranges from 20 nm to 60 nm.

17. The display device as claimed in claim **12**, wherein the first hole layer comprises a first hole transmission layer and an hole generating layer disposed on the second electron layer;

wherein the hole generating layer is configured to provide the first holes;

wherein the first hole transmission layer is configured to transport the first holes to the organic light-emitting layer.

18. The display device as claimed in claim **17**, wherein component materials of the first hole transmission layer comprise one or more selected from a group consisting of NPB, TDAPB, PIDATA, TDAB, BFA-1T, and TPTE, and a thickness of the first hole transmission layer ranges from 10 nm to 60 nm;

wherein component materials of the hole generating layer comprise one or more selected from a group consisting of HATCN, CuPc, and 2-TNATA, and a thickness of the hole generating layer ranges from 5 nm to 50 nm.

19. The display device as claimed in claim **12**, wherein the second electron layer comprises an electron generating layer and a second electron transmission layer disposed on the quantum dot light-emitting layer;

wherein the electron generating layer is configured to provide the second electrons;

wherein the second electron transmission layer is configured to transport the second electrons to the quantum dot light-emitting layer.

20. The display device as claimed in claim **19**, wherein component materials of the electron generating layer comprise organic materials and metal materials, and a thickness of the electron generating layer ranges from 5 nm to 50 nm;

wherein component materials of the second electron transmission layer comprise one or more selected from a group consisting of BCP, TmPyPb, Bphen, TRZ,

OXD-7, TAZ, TPBI, and TPyPhB, and a thickness of the second electron transmission layer ranges from 20 nm to 60 nm.

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专利名称(译)	量子点发光二极管和显示装置		
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申请号	US15/576703	申请日	2017-11-09
[标]申请(专利权)人(译)	深圳市华星光电技术有限公司		
[标]发明人	YUAN WEI JIAO SHIBO		
发明人	YUAN, WEI JIAO, SHIBO		
IPC分类号	H01L51/50 H01L51/00		
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摘要(译)

本发明提供一种量子点发光二极管，包括第一电子层，有机发光层，第一空穴层，第二电子层，量子点发光层和第二空穴层。第一电子层和第一空穴层被配置为将第一电子和第一空穴传输到有机发光层。有机发光层配置为通过重新组合第一电子和第一空穴来发射第一光。第二电子层和第二空穴层被配置为将第二电子和第二空穴传输到量子点发光层。量子点发光层配置为通过重新组合第二电子和第二空穴来发射第二光。

